Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Materia	al:
Glass and metal	
Overall Length:	
0.190 inches	
Overall Diameter	·
Between 0.592 inc	ches and 0.660 inches
Internal Configur	ration:
Junction contact	
Electrode Interna	ally-electrically Connected To Case:
Gate	
Mounting Metho	d:
Press fit	
Features Provide	ed:
Hermetically seale	ed case
Semiconductor M	Material:
Silicon	
Voltage Rating Ir	n Volts Per Characteristic:
100.0 repetitive p	beak reverse voltage
Current Rating P	Per Characteristic:
12.00 amperes for	rward current, total rms watts
Power Rating Pe	r Characteristic:
5.0 watts small-sig	gnal input power, common-collector blank
Maximum Opera	ting Tempurature Per Measurement Point:
110.0 degrees cel	lsius ambient air
Special Features	:
Junction pattern a	irrangement: pnpn
Test Data Docum	nent:
82577-925947 dra	awing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any spec	cification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type A	nd Quantity:
3 ribbon	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
A110a0	